



# PSMN8R5-40MLD

N-channel 40 V, 8.5 mΩ, logic level MOSFET in LPAK33 using NextPower-S3 technology

10 February 2020

Product data sheet

## 1. General description

60 A, logic level N-channel enhancement mode MOSFET in 175 °C LPAK33 package using advanced TrenchMOS Superjunction technology. This product has been designed and qualified for high efficiency applications at high switching frequencies.

## 2. Features and benefits

- Avalanche rated, 100% tested
- NextPower-S3 technology delivers 'superfast switching with soft body-diode recovery'
- Low  $Q_{RR}$ ,  $Q_G$  and  $Q_{GD}$  for high system efficiency, especially at high switching frequencies
- Low spiking and ringing for low EMI designs
- High reliability clip bonded and solder die attach Mini Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Exposed leads can be wave soldered, visual solder joint inspection and high quality solder joints
- Low parasitic inductance and resistance

## 3. Applications

- Secondary side synchronous rectification
- DC-to-DC converters
- Brushless DC motor drive
- LED lighting

## 4. Quick reference data

Table 1. Quick reference data

| Symbol                  | Parameter                        | Conditions                                                                                                                |     | Min | Typ | Max | Unit |
|-------------------------|----------------------------------|---------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|-----|------|
| V <sub>DS</sub>         | drain-source voltage             | 25 °C ≤ T <sub>j</sub> ≤ 175 °C                                                                                           |     | -   | -   | 40  | V    |
| I <sub>D</sub>          | drain current                    | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>                                                   | [1] | -   | -   | 60  | A    |
| T <sub>j</sub>          | junction temperature             |                                                                                                                           |     | -55 | -   | 175 | °C   |
| Static characteristics  |                                  |                                                                                                                           |     |     |     |     |      |
| R <sub>DSon</sub>       | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>                            |     | -   | 7.2 | 8.5 | mΩ   |
|                         |                                  | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>                           |     | -   | 9   | 11  | mΩ   |
| Dynamic characteristics |                                  |                                                                                                                           |     |     |     |     |      |
| Q <sub>GD</sub>         | gate-drain charge                | I <sub>D</sub> = 15 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 4.5 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a> |     | 0.6 | 2.1 | 4.2 | nC   |

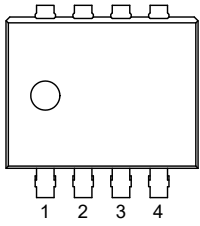
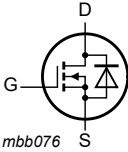
## N-channel 40 V, 8.5 mΩ, logic level MOSFET in LPAK33 using NextPower-S3 technology

| Symbol       | Parameter         | Conditions                                                                                                                   | Min | Typ | Max | Unit |
|--------------|-------------------|------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| $Q_{G(tot)}$ | total gate charge | $I_D = 15\text{ A}$ ; $V_{DS} = 20\text{ V}$ ; $V_{GS} = 10\text{ V}$ ;<br><a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a> | 12  | 19  | 27  | nC   |

[1] 60A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                                                                                    | Graphic symbol                                                                                |
|-----|--------|-----------------------------------|-------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------|
| 1   | S      | source                            | <br>LPAK33 (SOT1210) | <br>mbb076 |
| 2   | S      | source                            |                                                                                                       |                                                                                               |
| 3   | S      | source                            |                                                                                                       |                                                                                               |
| 4   | G      | gate                              |                                                                                                       |                                                                                               |
| mb  | D      | Mounting base; connected to drain |                                                                                                       |                                                                                               |

## 6. Marking

Table 3. Marking codes

| Type number   | Marking code |
|---------------|--------------|
| PSMN8R5-40MLD | 8D5L40       |

## 7. Limiting values

Table 4. Limiting values

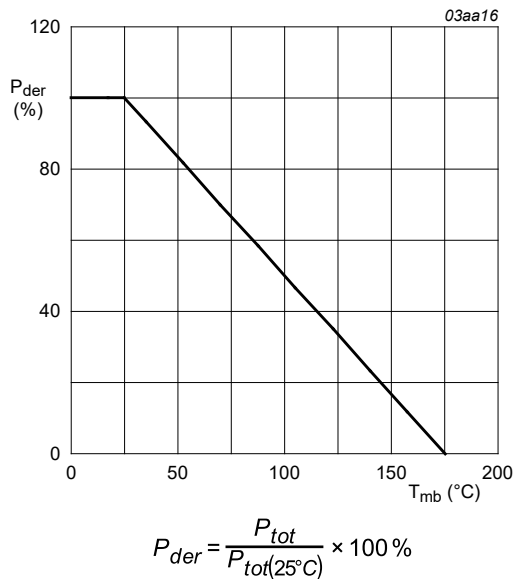
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                    | Parameter                  | Conditions                                                                                   | Min | Max | Unit |
|---------------------------|----------------------------|----------------------------------------------------------------------------------------------|-----|-----|------|
| $V_{DS}$                  | drain-source voltage       | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                                   | -   | 40  | V    |
| $V_{DSM}$                 | peak drain-source voltage  | $t_p \leq 20\text{ ns}$ ; $f \leq 500\text{ kHz}$ ; $E_{DS(AL)} \leq 200\text{ nJ}$ ; pulsed | -   | 45  | V    |
| $V_{DGR}$                 | drain-gate voltage         | $25\text{ °C} \leq T_j \leq 175\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$                    | -   | 40  | V    |
| $V_{GS}$                  | gate-source voltage        |                                                                                              | -20 | 20  | V    |
| $P_{tot}$                 | total power dissipation    | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                                             | -   | 59  | W    |
| $I_D$                     | drain current              | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>                    | [1] | 60  | A    |
|                           |                            | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; <a href="#">Fig. 2</a>                   | -   | 42  | A    |
| $I_{DM}$                  | peak drain current         | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 3</a>  | -   | 239 | A    |
| $T_{stg}$                 | storage temperature        |                                                                                              | -55 | 175 | °C   |
| $T_j$                     | junction temperature       |                                                                                              | -55 | 175 | °C   |
| $T_{sld(M)}$              | peak soldering temperature |                                                                                              | -   | 260 | °C   |
| <b>Source-drain diode</b> |                            |                                                                                              |     |     |      |
| $I_S$                     | source current             | $T_{mb} = 25\text{ °C}$                                                                      | -   | 59  | A    |
| $I_{SM}$                  | peak source current        | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$                           | -   | 239 | A    |

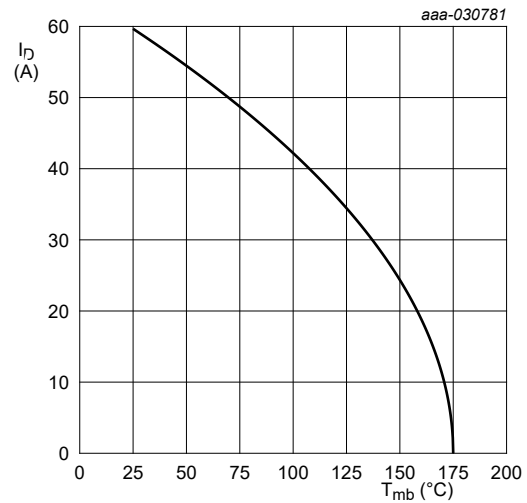
## N-channel 40 V, 8.5 mΩ, logic level MOSFET in LPAK33 using NextPower-S3 technology

| Symbol                      | Parameter                                    | Conditions                                                                                                                                                             |     | Min | Max | Unit |
|-----------------------------|----------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| <b>Avalanche ruggedness</b> |                                              |                                                                                                                                                                        |     |     |     |      |
| E <sub>DS(AL)S</sub>        | non-repetitive drain-source avalanche energy | I <sub>D</sub> = 25 A; V <sub>sup</sub> ≤ 40 V; R <sub>GS</sub> = 50 Ω;<br>V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped;<br>t <sub>p</sub> = 80 μs  | [2] | -   | 46  | mJ   |
|                             |                                              | I <sub>D</sub> = 15 A; V <sub>sup</sub> ≤ 40 V; R <sub>GS</sub> = 50 Ω;<br>V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped;<br>t <sub>p</sub> = 180 μs | [2] | -   | 70  | mJ   |

- [1] 60A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Protected by 100% test



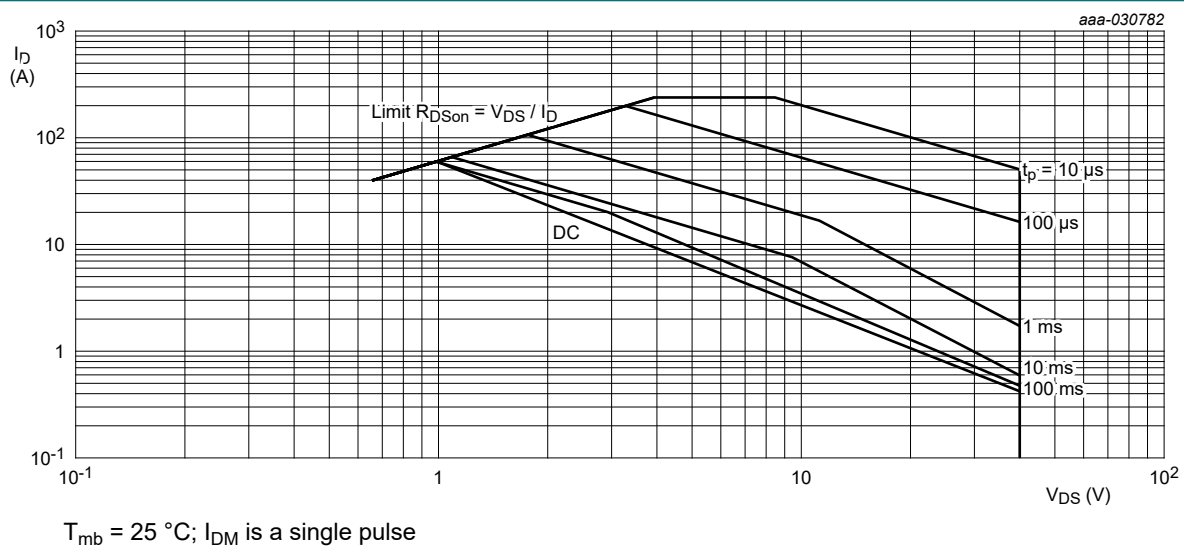
**Fig. 1. Normalized total power dissipation as a function of mounting base temperature**



V<sub>GS</sub> ≥ 10 V

(1) 60A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

**Fig. 2. Continuous drain current as a function of mounting base temperature**



**Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

## 8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter                                         | Conditions | Min | Typ  | Max  | Unit |
|----------------|---------------------------------------------------|------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 4     | -   | 2.33 | 2.56 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | Fig. 5     | -   | 50   | -    | K/W  |
|                |                                                   | Fig. 6     | -   | 130  | -    | K/W  |

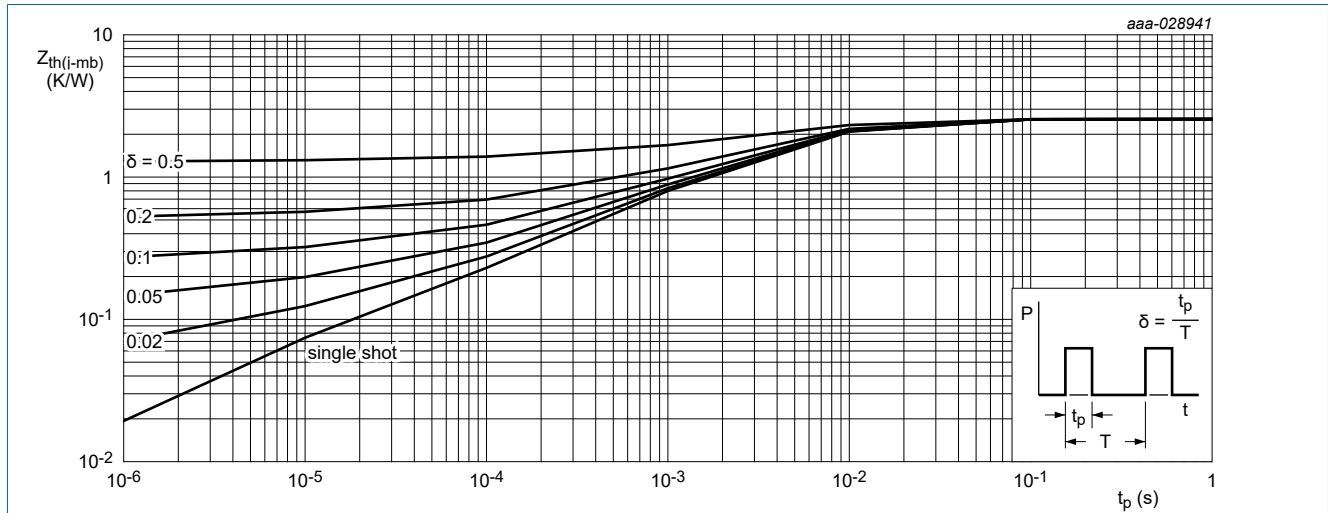


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

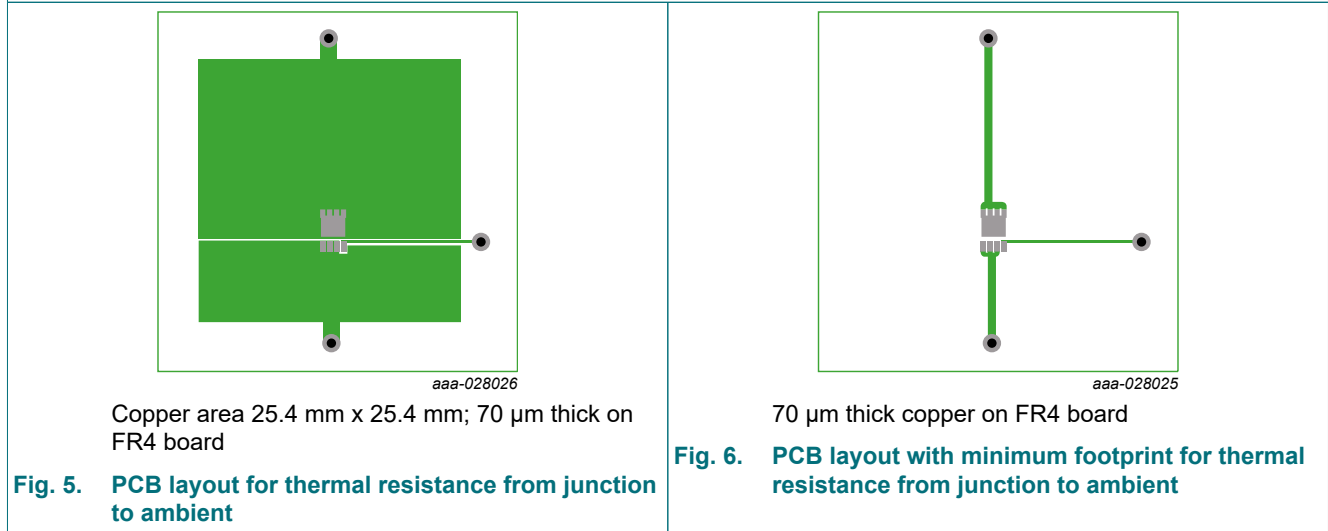


Fig. 5. PCB layout for thermal resistance from junction to ambient

Fig. 6. PCB layout with minimum footprint for thermal resistance from junction to ambient

## 9. Characteristics

Table 6. Characteristics

| Symbol                        | Parameter                      | Conditions                                                | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------|-----------------------------------------------------------|-----|-----|-----|------|
| <b>Static characteristics</b> |                                |                                                           |     |     |     |      |
| $V_{(BR)DSS}$                 | drain-source breakdown voltage | $I_D = 250 \mu A$ ; $V_{GS} = 0 V$ ; $T_j = 25 ^\circ C$  | 40  | -   | -   | V    |
|                               |                                | $I_D = 250 \mu A$ ; $V_{GS} = 0 V$ ; $T_j = -55 ^\circ C$ | 36  | -   | -   | V    |

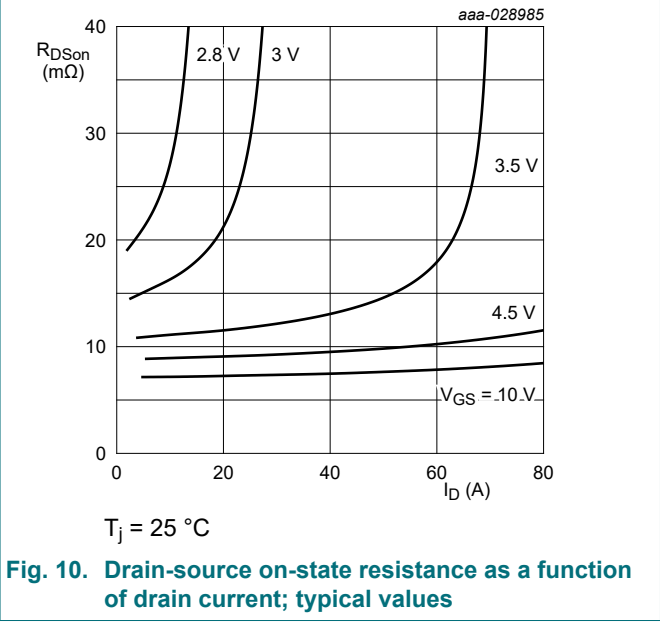
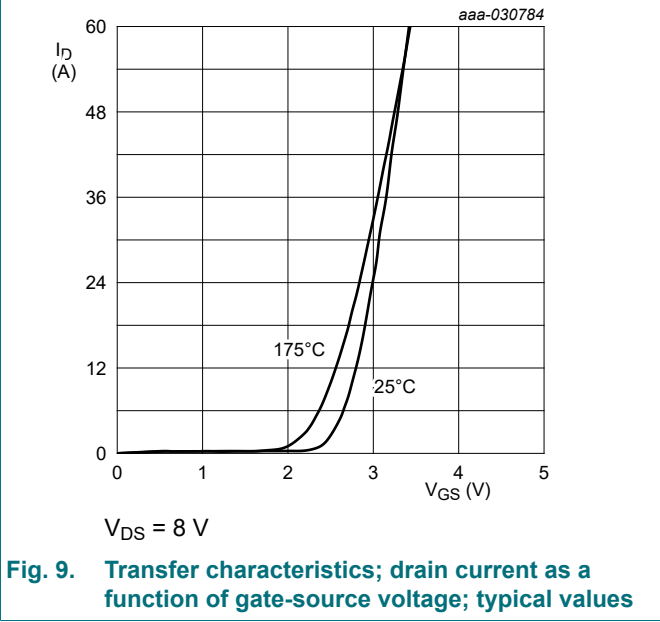
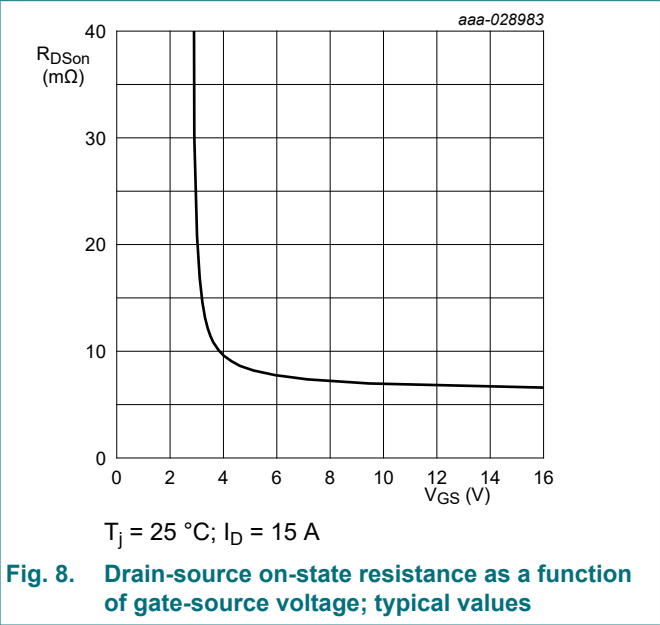
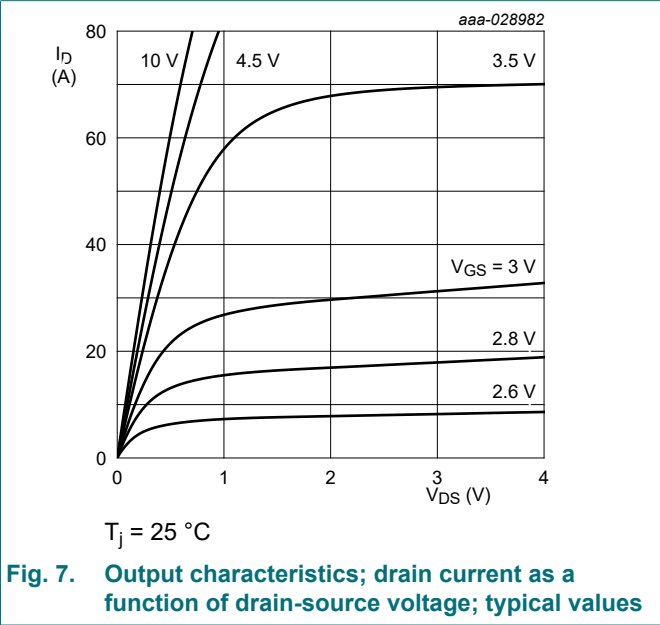
## N-channel 40 V, 8.5 mΩ, logic level MOSFET in LPAK33 using NextPower-S3 technology

| Symbol                         | Parameter                                                | Conditions                                                                                                                           | Min  | Typ  | Max  | Unit          |
|--------------------------------|----------------------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------|------|------|------|---------------|
| $V_{GS(th)}$                   | gate-source threshold voltage                            | $I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ }^\circ\text{C}$                                                         | 1.45 | 1.77 | 2.15 | V             |
| $\Delta V_{GS(th)}/\Delta T$   | gate-source threshold voltage variation with temperature | $25 \text{ }^\circ\text{C} \leq T_j \leq 150 \text{ }^\circ\text{C}$                                                                 | -    | -4.2 | -    | mV/K          |
| $I_{DSS}$                      | drain leakage current                                    | $V_{DS} = 32 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$                                                 | -    | -    | 1    | $\mu\text{A}$ |
|                                |                                                          | $V_{DS} = 32 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 125 \text{ }^\circ\text{C}$                                                | -    | 0.3  | -    | $\mu\text{A}$ |
| $I_{GSS}$                      | gate leakage current                                     | $V_{GS} = 16 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$                                                 | -    | 2    | 100  | nA            |
|                                |                                                          | $V_{GS} = -16 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$                                                | -    | 2    | 100  | nA            |
| $R_{DS(on)}$                   | drain-source on-state resistance                         | $V_{GS} = 10 \text{ V}$ ; $I_D = 15 \text{ A}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>                         | -    | 7.2  | 8.5  | mΩ            |
|                                |                                                          | $V_{GS} = 10 \text{ V}$ ; $I_D = 15 \text{ A}$ ; $T_j = 175 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>                        | -    | -    | 16.5 | mΩ            |
|                                |                                                          | $V_{GS} = 4.5 \text{ V}$ ; $I_D = 15 \text{ A}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>                        | -    | 9    | 11   | mΩ            |
|                                |                                                          | $V_{GS} = 4.5 \text{ V}$ ; $I_D = 15 \text{ A}$ ; $T_j = 175 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>                       | -    | -    | 21.4 | mΩ            |
| $R_G$                          | gate resistance                                          | $f = 1 \text{ MHz}$ ; $T_j = 25 \text{ }^\circ\text{C}$                                                                              | 0.3  | 0.8  | 2    | Ω             |
| <b>Dynamic characteristics</b> |                                                          |                                                                                                                                      |      |      |      |               |
| $Q_{G(tot)}$                   | total gate charge                                        | $I_D = 15 \text{ A}$ ; $V_{DS} = 20 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>         | 12   | 19   | 27   | nC            |
|                                |                                                          | $I_D = 15 \text{ A}$ ; $V_{DS} = 20 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>        | 6    | 9    | 13   | nC            |
|                                |                                                          | $I_D = 0 \text{ A}$ ; $V_{DS} = 0 \text{ V}$ ; $V_{GS} = 10 \text{ V}$                                                               | -    | 10   | -    | nC            |
| $Q_{GS}$                       | gate-source charge                                       | $I_D = 15 \text{ A}$ ; $V_{DS} = 20 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>        | 2.1  | 3.6  | 5.4  | nC            |
| $Q_{GS(th)}$                   | pre-threshold gate-source charge                         |                                                                                                                                      | 1.2  | 2.1  | 3.2  | nC            |
| $Q_{GS(th-pl)}$                | post-threshold gate-source charge                        |                                                                                                                                      | 0.9  | 1.5  | 2.3  | nC            |
| $Q_{GD}$                       | gate-drain charge                                        |                                                                                                                                      | 0.6  | 2.1  | 4.2  | nC            |
| $V_{GS(pl)}$                   | gate-source plateau voltage                              | $I_D = 15 \text{ A}$ ; $V_{DS} = 20 \text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>                                   | -    | 2.8  | -    | V             |
| $C_{iss}$                      | input capacitance                                        | $V_{DS} = 20 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $f = 1 \text{ MHz}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 14</a> | 842  | 1296 | 1814 | pF            |
| $C_{oss}$                      | output capacitance                                       |                                                                                                                                      | 249  | 383  | 536  | pF            |
| $C_{rss}$                      | reverse transfer capacitance                             |                                                                                                                                      | 15   | 49   | 108  | pF            |
| $t_{d(on)}$                    | turn-on delay time                                       | $V_{DS} = 20 \text{ V}$ ; $R_L = 1.2 \text{ } \Omega$ ; $V_{GS} = 4.5 \text{ V}$ ; $R_{G(ext)} = 5 \text{ } \Omega$                  | -    | 9.5  | -    | ns            |
| $t_r$                          | rise time                                                |                                                                                                                                      | -    | 9.4  | -    | ns            |
| $t_{d(off)}$                   | turn-off delay time                                      |                                                                                                                                      | -    | 11   | -    | ns            |
| $t_f$                          | fall time                                                |                                                                                                                                      | -    | 5.6  | -    | ns            |
| $Q_{oss}$                      | output charge                                            | $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 20 \text{ V}$ ; $f = 1 \text{ MHz}$ ; $T_j = 25 \text{ }^\circ\text{C}$                           | -    | 11.4 | -    | nC            |
| <b>Source-drain diode</b>      |                                                          |                                                                                                                                      |      |      |      |               |
| $V_{SD}$                       | source-drain voltage                                     | $I_S = 15 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 15</a>                          | -    | 0.85 | 1    | V             |

N-channel 40 V, 8.5 mΩ, logic level MOSFET in LPAK33 using NextPower-S3 technology

| Symbol   | Parameter                  | Conditions                                                                                                                                |     | Min | Typ | Max | Unit |
|----------|----------------------------|-------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|-----|------|
| $t_{rr}$ | reverse recovery time      | $I_S = 15\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ;<br>$V_{DS} = 20\text{ V}$ ; <a href="#">Fig. 16</a> |     | -   | 22  | -   | ns   |
| $Q_r$    | recovered charge           |                                                                                                                                           | [1] | -   | 15  | -   | nC   |
| $t_a$    | reverse recovery rise time |                                                                                                                                           |     | -   | 13  | -   | ns   |
| $t_b$    | reverse recovery fall time |                                                                                                                                           |     | -   | 8.2 | -   | ns   |

[1] includes capacitive recovery



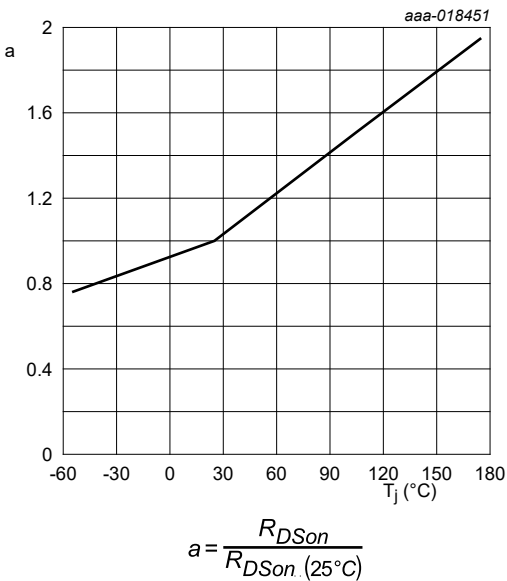


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

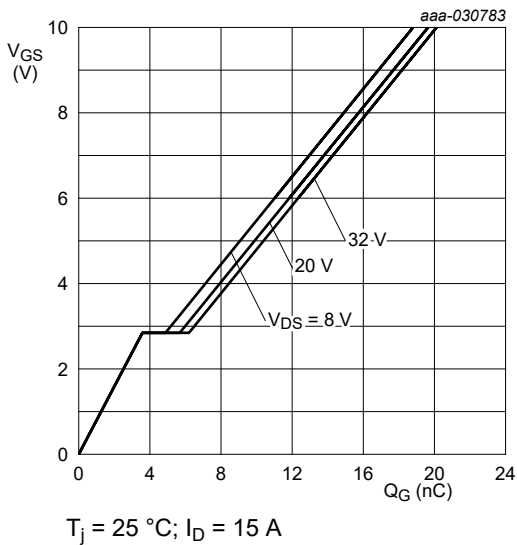


Fig. 12. Gate-source voltage as a function of gate charge; typical values

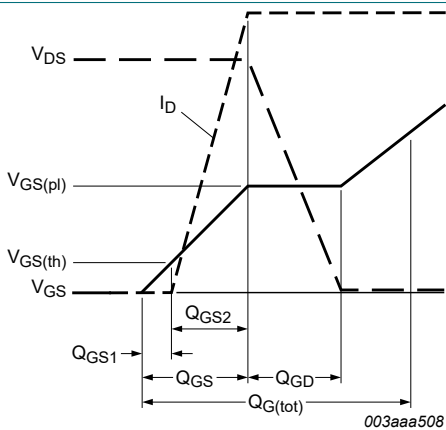


Fig. 13. Gate charge waveform definitions

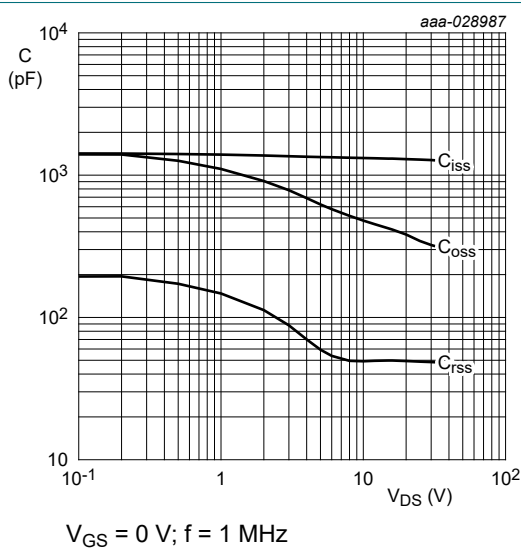
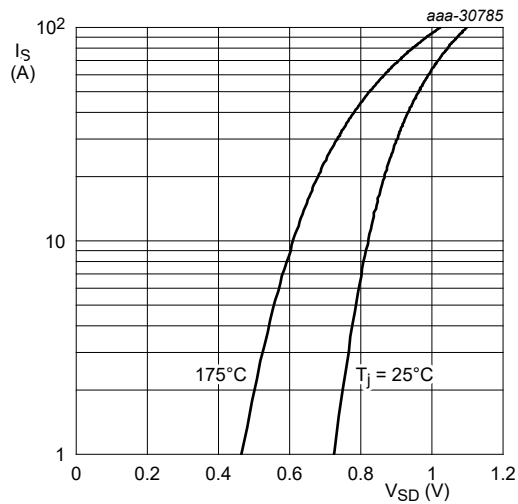


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0\text{ V}$

Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

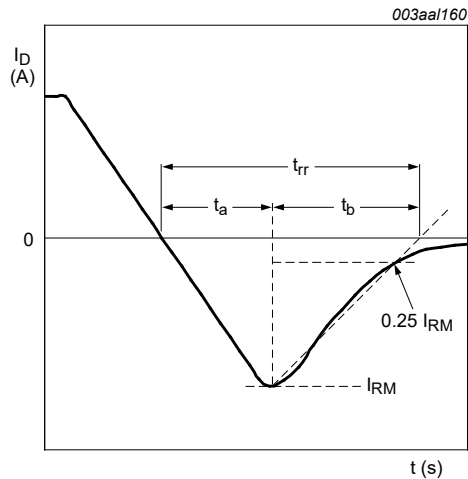


Fig. 16. Reverse recovery timing definition

10. Package outline



Fig. 17. Package outline LPAK33 (SOT1210)

11. Soldering

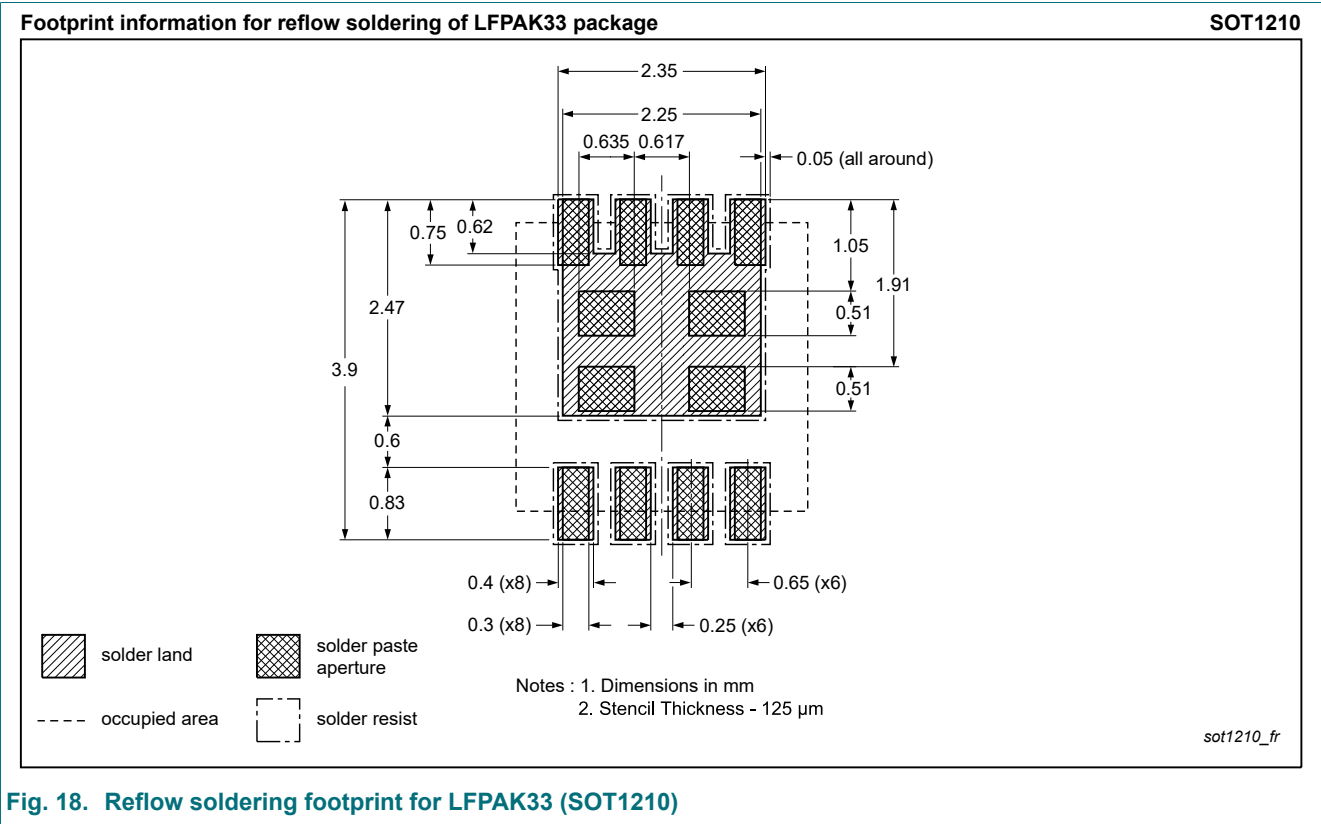


Fig. 18. Reflow soldering footprint for LPAK33 (SOT1210)

## 12. Legal information

### Data sheet status

| Document status<br>[1][2]      | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <https://www.nexperia.com>.

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